# imall

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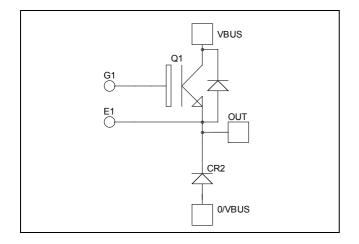
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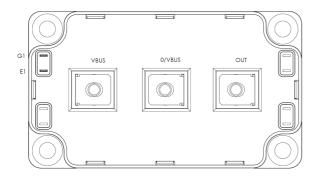
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





### Buck chopper Trench + Field Stop IGBT3 Power Module





### $V_{CES} = 600V$ $I_C = 300A$ @ Tc = 80°C

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
  - Kelvin emitter for easy drive
  - Very low stray inductance
    - Symmetrical design
    - M5 power connectors
  - High level of integration

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		600	V
I <sub>C</sub>	Continuous Collector Current	$T_C = 25^{\circ}C$	430	
	Continuous Conector Current	$T_C = 80^{\circ}C$	300	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	500	
$V_{GE}$	Gate – Emitter Voltage		$\pm 20$	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1150	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	600A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				350	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_{C} = 300A$	$T_j = 25^{\circ}C$		1.4	1.8	V
V <sub>CE(sat)</sub>			$T_{j} = 150^{\circ}C$		1.5		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				500	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			24			
Coes	Output Capacitance				1.5		nF	
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.75				
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switchi	ng (25°C)		115			
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			45			
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 300A$ $R_{G} = 1.8\Omega$			200		ns	
$T_{\rm f}$	Fall Time				55			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$			120		ns	
Tr	Rise Time				50			
T <sub>d(off)</sub>	Turn-off Delay Time				250			
T <sub>f</sub>	Fall Time	$R_G = 1.8\Omega$			70			
Б	Town on Engineer	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		1.5			
Eon	Turn on Energy	$V_{Bus} = 300V$		$T_{j} = 150^{\circ}C$		2.7		mJ
Б			$T_j = 25^{\circ}C$		8.55		mJ	
E <sub>off</sub> Turn off Energy	Turn on Energy	$R_G = 1.8\Omega$	$T_{j} = 150^{\circ}C$		10.5		IIIJ	

### Chopper diode ratings and characteristics

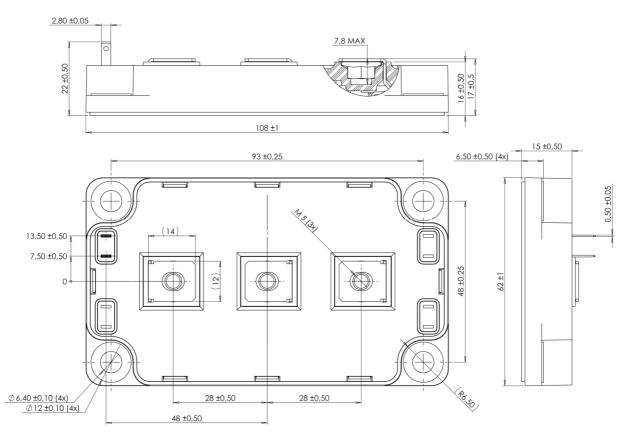
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	$V_{R} = 600 V$	$T_i = 25^{\circ}C$			150	μA
	<u> </u>		$T_j = 150^{\circ}C$			400	
$l_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		300		A
Vr		$I_{\rm F} = 300 {\rm A}$	$T_i = 25^{\circ}C$		1.5	1.9	V
▼ F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.4		•
t <sub>rr</sub>	Reverse Recovery Time	$I_{F} = 300A$ $V_{R} = 300V$ $di/dt = 3100A/\mu s$	$T_j = 25^{\circ}C$		130		ns
ι <sub>rr</sub>			$T_{j} = 150^{\circ}C$		225		
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$		13.5		μC
			$T_{j} = 150^{\circ}C$		28.5		μυ
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		3.5		mJ
			$T_{j} = 150^{\circ}C$		7.1		1115



### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance IGBT Diode				0.13	°C/W	
<b>R</b> <sub>th</sub> JC			Diode			0.21	C/ W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		175	°C
T <sub>STG</sub>	Storage Temperature Range			-40		125	
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

### SP6 Package outline (dimensions in mm)



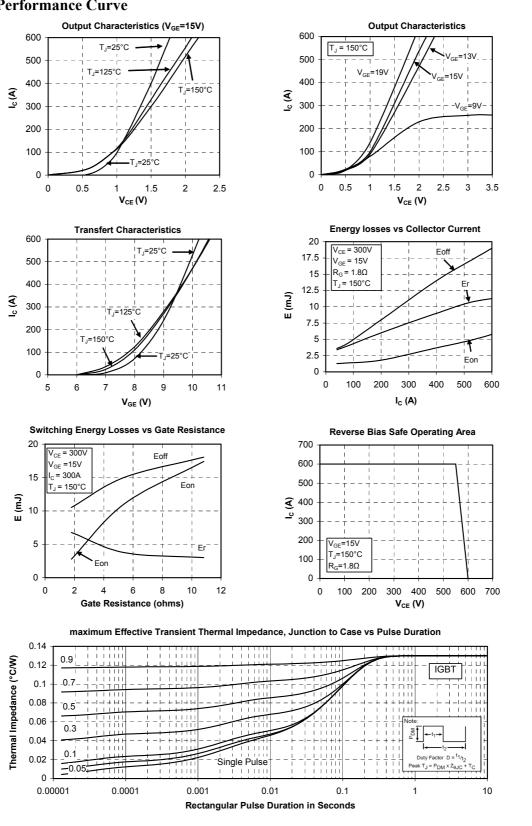
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

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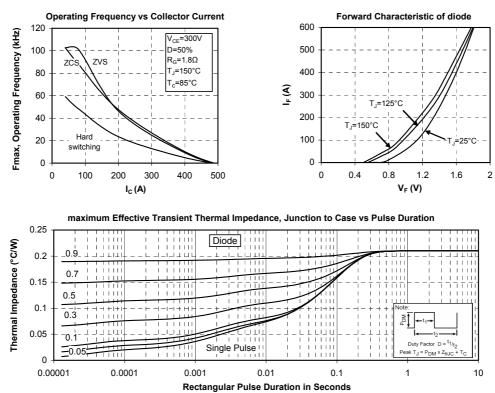


### **Typical Performance Curve**



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